

# **NX2301P**

# 20 V, 2 A P-channel Trench MOSFET Rev. 1 — 26 October 2010

Product data sheet

## **Product profile**

## 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- 1.8 V R<sub>DSon</sub> rated for Low Voltage Gate Drive
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

## 1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_{amb} = 25  ^{\circ}C$	-	-	-20	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	-	±8	V
$I_D$	drain current	$T_{amb}$ = 25 °C; $V_{GS}$ = -4.5 V	[1] _	-	-2	Α
R <sub>DSon</sub>	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = -4.5 \text{V};$ $I_D = -1 \text{A}$	<u>[2]</u> -	100	120	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm $^2$ , t  $\leq$  5 s.



<sup>[2]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.01.$ 

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# 2. Pinning information

Table 2. Pinning

Idbic 2.	i iiiiiiig			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	<u>    3</u>	
3	D	drain	1 2	G S
				017aaa094

# 3. Ordering information

Table 3. Ordering information

Type number	Package	Package		
	Name	Description	Version	
NX2301P	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
NX2301P	MG*

<sup>[1] \* =</sup> placeholder for manufacturing site code

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

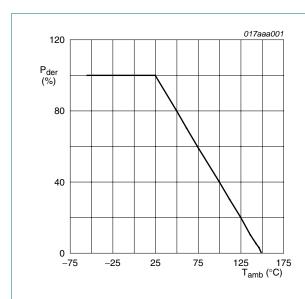
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>amb</sub> = 25 °C	-	-20	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	±8	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}$	<u>[1]</u>		
		T <sub>amb</sub> = 25 °C	-	-2	Α
		T <sub>amb</sub> = 100 °C	-	-1.2	Α
$I_{DM}$	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs	-	-6	Α

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**Table 5.** Limiting values ...continued
In accordance with the Absolute Maximum Rating System (IEC 60134).

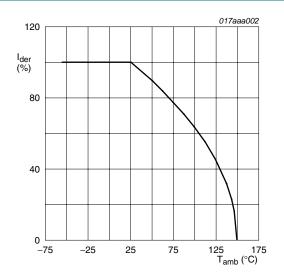
Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub> total	total power dissipation	otal power dissipation T <sub>amb</sub> = 25 °C	[2] -	400	mW
			[1] -	710	mW
		$T_{sp} = 25  ^{\circ}C$	-	2.8	W
Tj	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C
Source-d	rain diode				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> -	-0.7	Α

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm $^2$ , t  $\leq$  5 s.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$ 

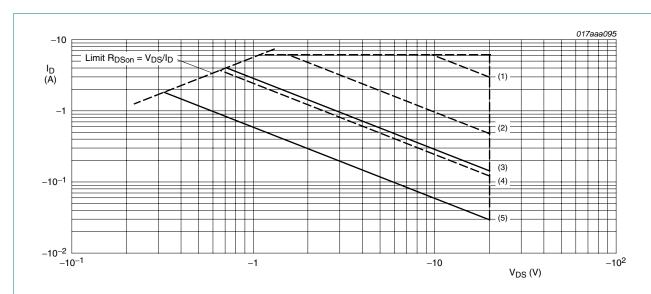
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

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I<sub>DM</sub> = single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3) DC;  $T_{sp} = 25 \, ^{\circ}C$
- (4)  $t_p = 100 \text{ ms}$
- (5) DC;  $T_{amb} = 25 \, ^{\circ}C$ ; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

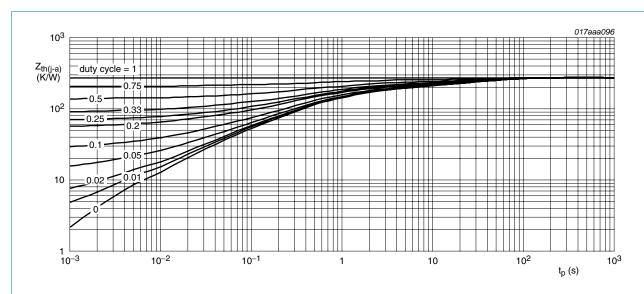
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> -	-	315	K/W
			[2] _	-	175	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	45	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

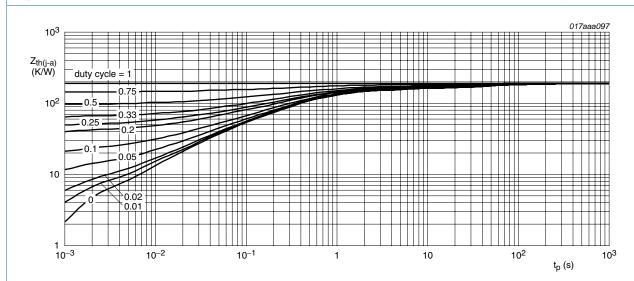
<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm $^2$ , t  $\leq$  5 s.

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FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 20 V, 2 A P-channel Trench MOSFET

## 7. Characteristics

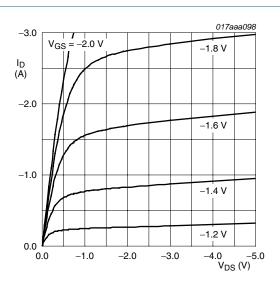
**Table 7. Characteristics** 

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V$	-20	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}$	-0.5	-0.75	-1.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}$	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = \pm 8 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	±100	nA
R <sub>DSon</sub>	drain-source on-state		<u>[1]</u>			
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1 \text{ A}$				
		T <sub>j</sub> = 25 °C		100	120	$m\Omega$
		T <sub>j</sub> = 150 °C		-	180	$m\Omega$
		$V_{GS} = -2.5 \text{ V}; I_D = -1 \text{ A}$	-	155	190	$m\Omega$
		$V_{GS} = -1.8 \text{ V};$ $I_D = -0.2 \text{ A}$	-	210	270	mΩ
<b>9</b> fs	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2 \text{ A}$	[1] -	4.7	-	S
Dynamic o	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = -2.2 \text{ A}; V_{DS} = -6 \text{ V};$	-	4.5	6	nC
$Q_{GS}$	gate-source charge	$V_{GS} = -4.5 \text{ V}$	-	1.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = -6 \text{ V};$	-	380	-	pF
C <sub>oss</sub>	output capacitance	f = 1 MHz	_	135	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	115	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DD} = -6 \text{ V};$	-	7	-	ns
t <sub>r</sub>	rise time	$R_L = 6 \Omega;$ - $V_{GS} = -4.5 V;$	-	15	-	ns
t <sub>d(off)</sub>	turn-off delay time	$R_{G} = 6 \Omega$	-	50	-	ns
t <sub>f</sub>	fall time		-	25	-	ns
Source-dr	ain diode					
$V_{SD}$	source-drain voltage	$I_S = -1 A; V_{GS} = 0 V$	<u>[1]</u> _	-0.8	-1.0	V

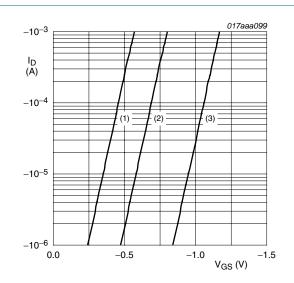
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.01.$ 

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 $T_{amb} = 25 \, ^{\circ}C$ 

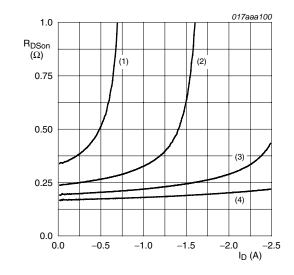
Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; \, V_{DS} = -10 \, V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

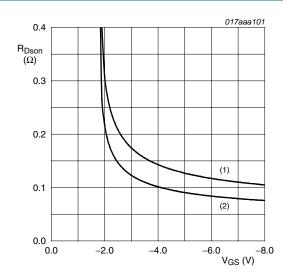


T<sub>amb</sub> = 25 °C

(1) 
$$V_{GS} = -1.4 \text{ V}$$

- (2)  $V_{GS} = -1.6 \text{ V}$
- (3)  $V_{GS} = -1.8 \text{ V}$
- (4)  $V_{GS} = -2.0 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



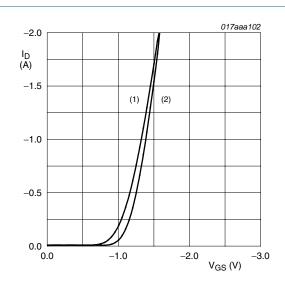
 $I_{D} = -2 A$ 

(1) 
$$T_{amb} = 125 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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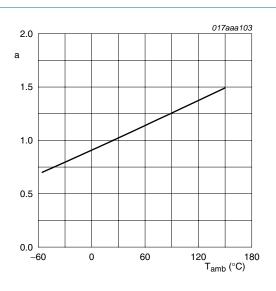


$$V_{DS} > I_{D} \times R_{DSon}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

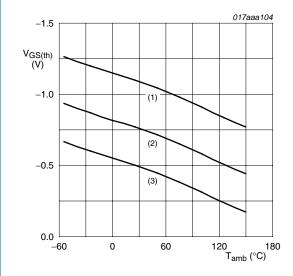
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

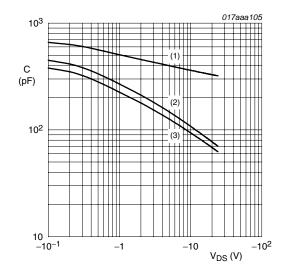
Fig 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

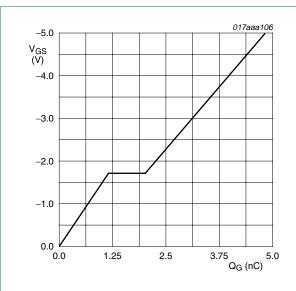
Fig 12. Gate-source threshold voltage as a function of ambient temperature



- (1) C<sub>iss</sub>
- (2) Coss
- $(3) \quad C_{rss}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 $I_D$  = -2 A;  $V_{DS}$  = -6 V;  $T_{amb}$  = 25 °C

Fig 14. Gate-source voltage as a function of gate charge; typical values

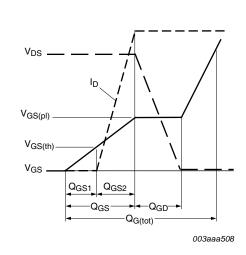
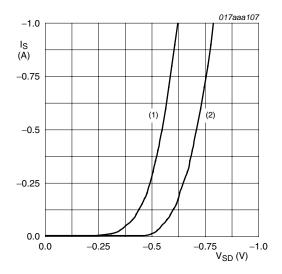


Fig 15. Gate charge waveform definitions



$$V_{GS} = 0 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

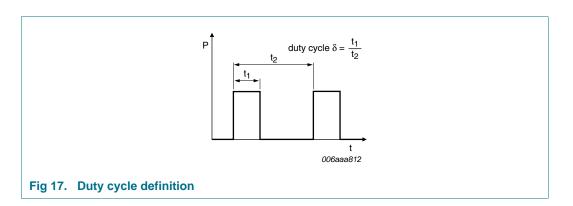
Fig 16. Source current as a function of source-drain voltage; typical values

<sup>(1)</sup>  $T_{amb} = 150 \, ^{\circ}C$ 

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20 V, 2 A P-channel Trench MOSFET

## **Test information**



## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 20 V, 2 A P-channel Trench MOSFET

# 9. Package outline

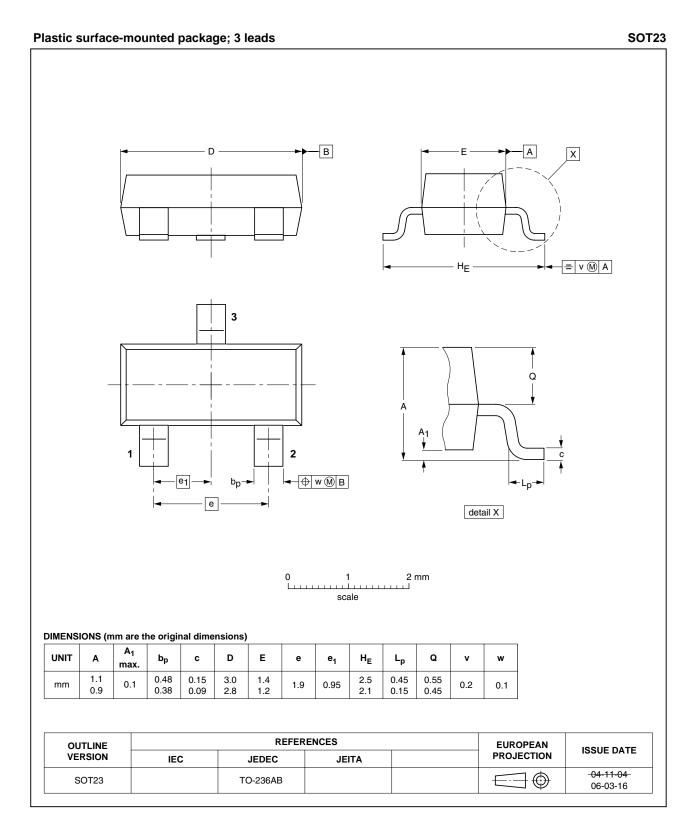


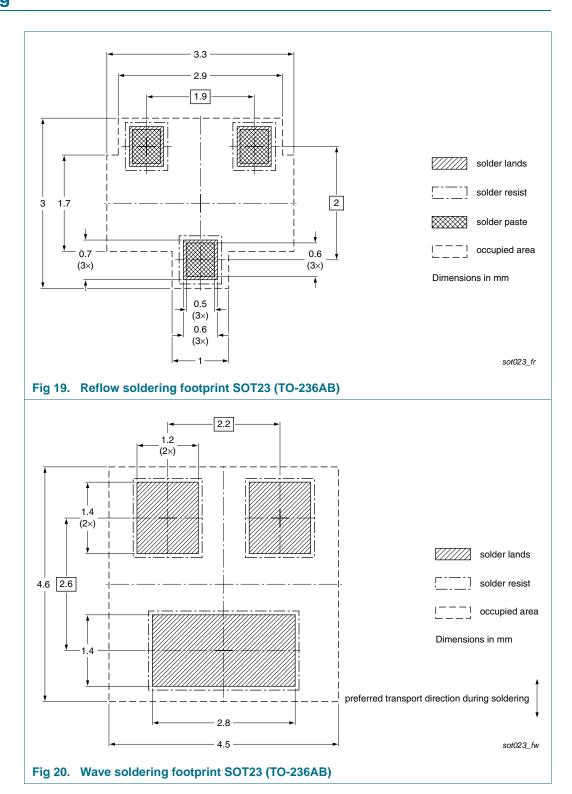
Fig 18. Package outline SOT23 (TO-236AB)

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# 10. Soldering



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## 20 V, 2 A P-channel Trench MOSFET

# 11. Revision history

#### Table 8. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX2301P v.1	20101026	Product data sheet	-	-

#### 20 V, 2 A P-channel Trench MOSFET

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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## 20 V, 2 A P-channel Trench MOSFET

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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For sales office addresses, please send an email to: salesaddresses@nxp.com

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